

TECHNICAL DATA
DATA SHEET 4556, REV. D

HERMETIC SCHOTTKY RECTIFIER

Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

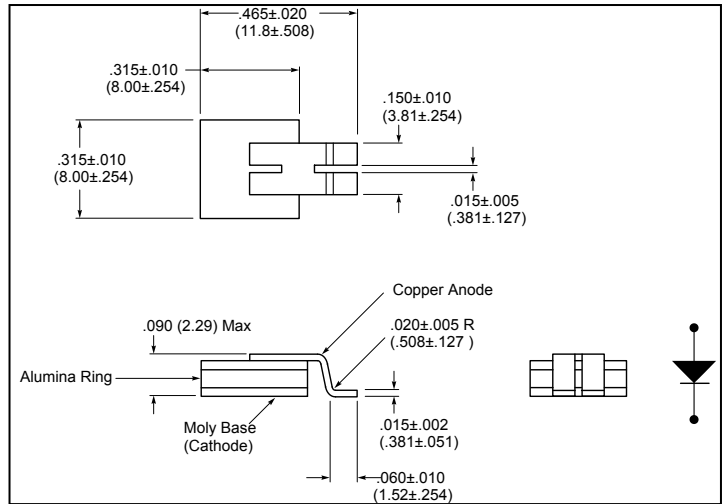
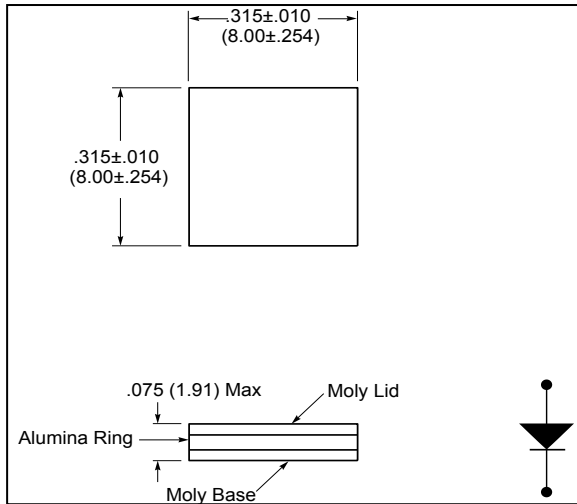
Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	60	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave	860	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25\text{ }^\circ\text{C}$, $I_{AS} = 3.0\text{ A}$, $L = 4.4\text{ mH}$	20	mJ
Repetitive Avalanche Current	I_{AR}	I_{AS} decay linearly to 0 in $1\text{ }\mu\text{s}$ f limited by T_J max $V_A=1.5V_R$	3.0	A
Maximum Thermal Resistance	$R_{\theta JC}$	DC operation	0.7	$^\circ\text{C/W}$
Max. Junction Temperature	T_J	-	-65 to +175	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$

Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 60A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.95	V
	V_{F2}	@ 60A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.79	V
Max. Reverse Current	I_{R1}	@ $V_R = 200\text{V}$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.3	mA
	I_{R2}	@ $V_R = 200\text{V}$, Pulse, $T_J = 125\text{ }^\circ\text{C}$	3.0	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV (p-p)}$	900	pF

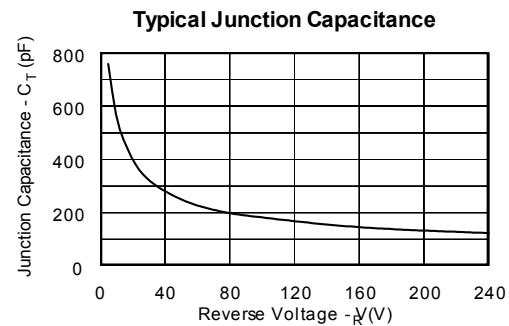
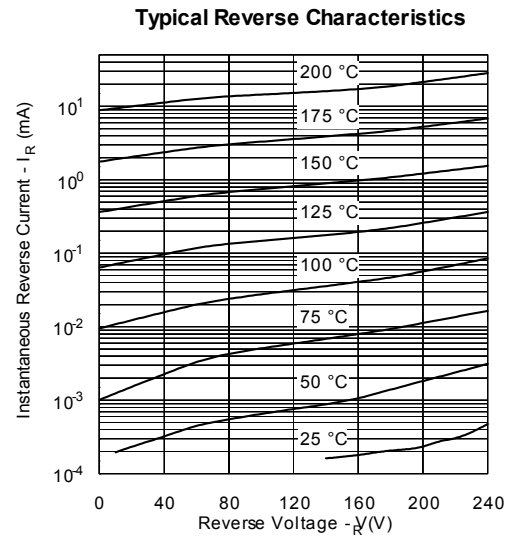
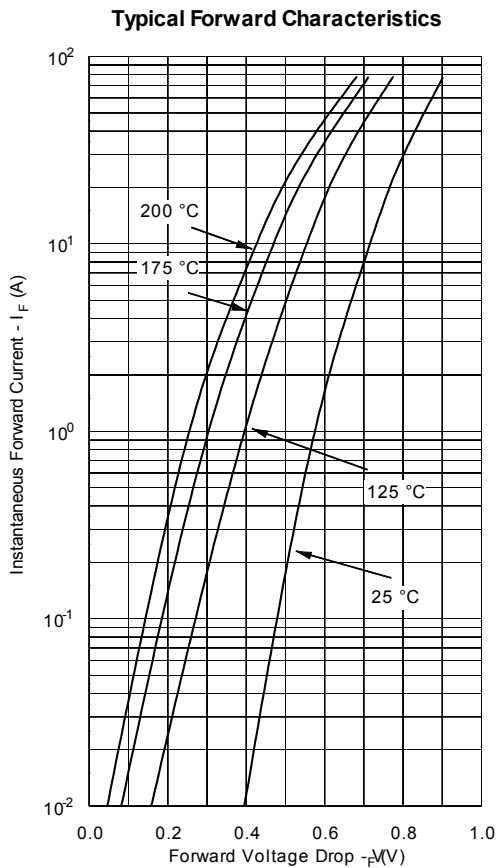
MECHANICAL DIMENSIONS: In Inches / mm



SHD-2

SHD-2B

Note: The V_f curves shown are for the unpackaged die only.



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